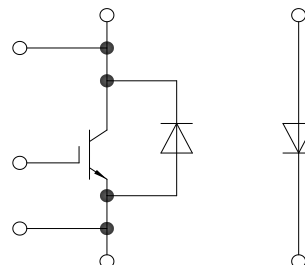
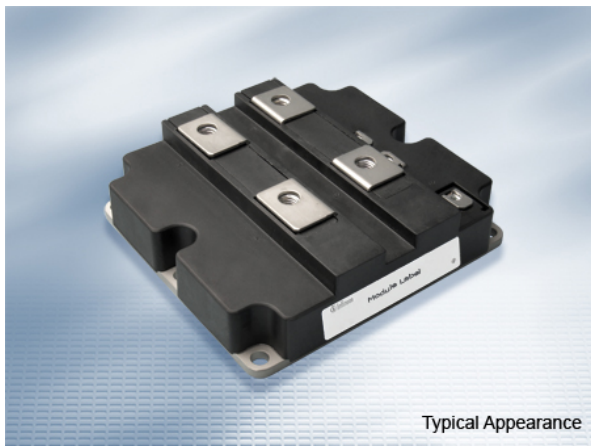


IHM-B 模块 采用斩波拓扑
IHM-B module with chopper configuration

初步数据 / Preliminary Data



$V_{CES} = 1700V$
 $I_{C\ nom} = 1200A / I_{CRM} = 2400A$

典型应用

- 斩波应用
- 大功率变流器
- 牵引变流器
- 风力发电机

Typical Applications

- Chopper Applications
- High Power Converters
- Traction Drives
- Wind Turbines

电气特性

- 提高工作结温 $T_{vj\ op}$
- 低 V_{CEsat}

Electrical Features

- Extended Operation Temperature $T_{vj\ op}$
- Low V_{CEsat}

机械特性

- 4 kV 交流 1分钟 绝缘
- 碳化硅铝 (AlSiC) 基板提供更高的温度循环能力
- 封装的 CTI > 400
- 高爬电距离和电气间隙
- 高功率循环和温度循环能力
- 高功率密度
- IHM B 封装

Mechanical Features

- 4 kV AC 1min Insulation
- AlSiC Base Plate for increased Thermal Cycling Capability
- Package with CTI > 400
- High Creepage and Clearance Distances
- High Power and Thermal Cycling Capability
- High Power Density
- IHM B Housing

Module Label Code

Barcode Code 128



Content of the Code

Digit

Module Serial Number	1 - 5
Module Material Number	6 - 11
Production Order Number	12 - 19
Datecode (Production Year)	20 - 21
Datecode (Production Week)	22 - 23

DMX - Code



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初步数据
Preliminary Data

IGBT, 制动-斩波器 / IGBT, Brake-Chopper
最大额定值 / Maximum Rated Values

集电极 - 发射极电压 Collector-emitter voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{CES}	1700	V
连续集电极直流电流 Continuous DC collector current	$T_C = 100^{\circ}\text{C}, T_{vj\max} = 175^{\circ}\text{C}$	$I_{C\text{nom}}$	1200	A
集电极重复峰值电流 Repetitive peak collector current	$t_P = 1\text{ms}$	I_{CRM}	2400	A
总功率损耗 Total power dissipation	$T_C = 25^{\circ}\text{C}, T_{vj\max} = 175^{\circ}\text{C}$	P_{tot}	7,05	kW
栅极 - 发射极峰值电压 Gate-emitter peak voltage		V_{GES}	+/-20	V

特征值 / Characteristic Values

			min.	typ.	max.	
集电极 - 发射极饱和电压 Collector-emitter saturation voltage	$I_C = 1200\text{A}, V_{GE} = 15\text{V}$ $I_C = 1200\text{A}, V_{GE} = 15\text{V}$ $I_C = 1200\text{A}, V_{GE} = 15\text{V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$V_{CE\text{sat}}$	1,90 2,30 2,40	2,25	V V V
栅极阈值电压 Gate threshold voltage	$I_C = 48,0\text{mA}, V_{CE} = V_{GE}, T_{vj} = 25^{\circ}\text{C}$		V_{GEth}	5,2	5,8	6,4 V
栅极电荷 Gate charge	$V_{GE} = -15\text{V} \dots +15\text{V}$		Q_G	13,0		μC
内部栅极电阻 Internal gate resistor	$T_{vj} = 25^{\circ}\text{C}$		R_{Gint}	1,6		Ω
输入电容 Input capacitance	$f = 1\text{MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{V}, V_{GE} = 0\text{V}$		C_{ies}	97,5		nF
反向传输电容 Reverse transfer capacitance	$f = 1\text{MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{V}, V_{GE} = 0\text{V}$		C_{res}	3,15		nF
集电极-发射极截止电流 Collector-emitter cut-off current	$V_{CE} = 1700\text{V}, V_{GE} = 0\text{V}, T_{vj} = 25^{\circ}\text{C}$		I_{CES}		5,0	mA
栅极-发射极漏电流 Gate-emitter leakage current	$V_{CE} = 0\text{V}, V_{GE} = 20\text{V}, T_{vj} = 25^{\circ}\text{C}$		I_{GES}		400	nA
开通延迟时间(电感负载) Turn-on delay time, inductive load	$I_C = 1200\text{A}, V_{CE} = 900\text{V}$ $V_{GE} = \pm 15\text{V}$ $R_{Gon} = 0,22\Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_{don}	0,70 0,75 0,75		μs μs μs
上升时间(电感负载) Rise time, inductive load	$I_C = 1200\text{A}, V_{CE} = 900\text{V}$ $V_{GE} = \pm 15\text{V}$ $R_{Gon} = 0,22\Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_r	0,13 0,14 0,15		μs μs μs
关断延迟时间(电感负载) Turn-off delay time, inductive load	$I_C = 1200\text{A}, V_{CE} = 900\text{V}$ $V_{GE} = \pm 15\text{V}$ $R_{Goff} = 0,9\Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_{doff}	1,10 1,20 1,25		μs μs μs
下降时间(电感负载) Fall time, inductive load	$I_C = 1200\text{A}, V_{CE} = 900\text{V}$ $V_{GE} = \pm 15\text{V}$ $R_{Goff} = 0,9\Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_f	0,30 0,50 0,55		μs μs μs
开通损耗能量(每脉冲) Turn-on energy loss per pulse	$I_C = 1200\text{A}, V_{CE} = 900\text{V}, L_S = 50\text{nH}$ $V_{GE} = \pm 15\text{V}$ $R_{Gon} = 0,22\Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{on}	250 350 370		mJ mJ mJ
关断损耗能量(每脉冲) Turn-off energy loss per pulse	$I_C = 1200\text{A}, V_{CE} = 900\text{V}, L_S = 50\text{nH}$ $V_{GE} = \pm 15\text{V}, du/dt = 3000\text{V}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $R_{Goff} = 0,9\Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{off}	330 440 470		mJ mJ mJ
短路数据 SC data	$V_{GE} \leq 15\text{V}, V_{CC} = 1000\text{V}$ $V_{CE\text{max}} = V_{CES} - L_{SCE} \cdot di/dt$ $t_P \leq 10\mu\text{s}, T_{vj} = 150^{\circ}\text{C}$		I_{SC}	4800		A
结 - 外壳热阻 Thermal resistance, junction to case	每个 IGBT / per IGBT		R_{thJC}		21,5	K/kW
外壳 - 散热器热阻 Thermal resistance, case to heatsink	每个 IGBT / per IGBT $\lambda_{\text{Paste}} = 1\text{W}/(\text{m}\cdot\text{K}) / \lambda_{\text{grease}} = 1\text{W}/(\text{m}\cdot\text{K})$		R_{thCH}		29,0	K/kW
在开关状态下温度 Temperature under switching conditions			$T_{vj\text{op}}$	-40	150	$^{\circ}\text{C}$

prepared by: WB	date of publication: 2013-11-05
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初步数据
Preliminary Data

二极管，制动-斩波器 / Diode, Brake-Chopper
最大额定值 / Maximum Rated Values

反向重复峰值电压 Repetitive peak reverse voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{RRM}	1700	V
连续正向直流电流 Continuous DC forward current		I_F	1200	A
正向重复峰值电流 Repetitive peak forward current	$t_P = 1\text{ ms}$	I_{FRM}	2400	A
I ² t-值 I ² t - value	$V_R = 0\text{ V}, t_P = 10\text{ ms}, T_{vj} = 125^{\circ}\text{C}$	I ² t	330	kA ² s
	$V_R = 0\text{ V}, t_P = 10\text{ ms}, T_{vj} = 150^{\circ}\text{C}$		310	kA ² s
最大损耗功率 Maximum power dissipation	$T_{vj} = 125^{\circ}\text{C}$	P_{RQM}	1600	kW
最小开通时间 Minimum turn-on time		$t_{on\ min}$	10,0	μs

特征值 / Characteristic Values

			min.	typ.	max.	
正向电压 Forward voltage	$I_F = 1200\text{ A}, V_{GE} = 0\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$		1,65	2,10	V
	$I_F = 1200\text{ A}, V_{GE} = 0\text{ V}$	$T_{vj} = 125^{\circ}\text{C}$	V_F	1,65		V
	$I_F = 1200\text{ A}, V_{GE} = 0\text{ V}$	$T_{vj} = 150^{\circ}\text{C}$		1,65		V
反向恢复峰值电流 Peak reverse recovery current	$I_F = 1200\text{ A}, -di_F/dt = 7700\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 900\text{ V}$ $V_{GE} = -15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$		1400		A
		$T_{vj} = 125^{\circ}\text{C}$	I_{RM}	1600		A
		$T_{vj} = 150^{\circ}\text{C}$		1600		A
恢复电荷 Recovered charge	$I_F = 1200\text{ A}, -di_F/dt = 7700\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 900\text{ V}$ $V_{GE} = -15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$		340		μC
		$T_{vj} = 125^{\circ}\text{C}$	Q_r	590		μC
		$T_{vj} = 150^{\circ}\text{C}$		660		μC
反向恢复损耗 (每脉冲) Reverse recovery energy	$I_F = 1200\text{ A}, -di_F/dt = 7700\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 900\text{ V}$ $V_{GE} = -15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$		210		mJ
		$T_{vj} = 125^{\circ}\text{C}$	E_{rec}	375		mJ
		$T_{vj} = 150^{\circ}\text{C}$		420		mJ
结 - 外壳热阻 Thermal resistance, junction to case	每个二极管 / per diode	R_{thJC}			29,0	K/kW
外壳 - 散热器热阻 Thermal resistance, case to heatsink	每个二极管 / per diode $\lambda_{Paste} = 1\text{ W}/(\text{m}\cdot\text{K}) / \lambda_{grease} = 1\text{ W}/(\text{m}\cdot\text{K})$	R_{thCH}		31,5		K/kW
在开关状态下温度 Temperature under switching conditions		$T_{vj\ op}$	-40		150	°C

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初步数据
Preliminary Data

反向二极管 / Diode, Reverse
最大额定值 / Maximum Rated Values

反向重复峰值电压 Repetitive peak reverse voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{RRM}	1700	V
连续正向直流电流 Continuous DC forward current		I_F	1200	A
正向重复峰值电流 Repetitive peak forward current	$t_P = 1\text{ ms}$	I_{FRM}	2400	A
I ² t-值 I ² t - value	$V_R = 0\text{ V}, t_P = 10\text{ ms}, T_{vj} = 125^{\circ}\text{C}$ $V_R = 0\text{ V}, t_P = 10\text{ ms}, T_{vj} = 150^{\circ}\text{C}$	I ² t	140 130	kA ² s kA ² s
最大损耗功率 Maximum power dissipation	$T_{vj} = 125^{\circ}\text{C}$	P_{RQM}	1200	kW
最小开通时间 Minimum turn-on time		$t_{on\ min}$	10,0	μs

特征值 / Characteristic Values

			min.	typ.	max.	
正向电压 Forward voltage	$I_F = 1200\text{ A}, V_{GE} = 0\text{ V}$ $I_F = 1200\text{ A}, V_{GE} = 0\text{ V}$ $I_F = 1200\text{ A}, V_{GE} = 0\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	V_F	1,80 1,90 1,95	2,20	V V V
反向恢复峰值电流 Peak reverse recovery current	$I_F = 1200\text{ A}, -di_F/dt = 7900\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 900\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	I_{RM}	1250 1350 1400		A A A
恢复电荷 Recovered charge	$I_F = 1200\text{ A}, -di_F/dt = 7900\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 900\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	Q_r	280 460 510		μC μC μC
反向恢复损耗 (每脉冲) Reverse recovery energy	$I_F = 1200\text{ A}, -di_F/dt = 7900\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 900\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{rec}	180 310 350		mJ mJ mJ
结 - 外壳热阻 Thermal resistance, junction to case	每个二极管 / per diode		R_{thJC}		37,5	K/kW
外壳 - 散热器热阻 Thermal resistance, case to heatsink	每个二极管 / per diode $\lambda_{Paste} = 1\text{ W}/(\text{m}\cdot\text{K}) / \lambda_{grease} = 1\text{ W}/(\text{m}\cdot\text{K})$		R_{thCH}		32,5	K/kW
在开关状态下温度 Temperature under switching conditions			$T_{vj\ op}$	-40	150	°C

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初步数据
Preliminary Data

模块 / Module

绝缘测试电压 Isolation test voltage	RMS, f = 50 Hz, t = 1 min.	V _{ISOL}	4,0		kV
模块基板材料 Material of module baseplate			AlSiC		
爬电距离 Creepage distance	端子- 散热片 / terminal to heatsink 端子- 端子 / terminal to terminal		32,2 32,2		mm
电气间隙 Clearance	端子- 散热片 / terminal to heatsink 端子- 端子 / terminal to terminal		19,1 19,1		mm
相对电痕指数 Comperative tracking index		CTI	> 400		
			min.	typ.	max.
杂散电感,模块 Stray inductance module		L _{sCE}		18	nH
模块引线电阻,端子-芯片 Module lead resistance, terminals - chip	T _c = 25°C, 每个开关 / per switch	R _{CC'+EE'} R _{AA'+CC'}		0,24 0,24	mΩ
储存温度 Storage temperature		T _{stg}	-40		150 °C
模块安装的安装扭矩 Mounting torque for modul mounting	螺丝 M6 根据相应的应用手册进行安装 Screw M6 - Mounting according to valid application note	M	4,25	-	5,75 Nm
端子联接扭矩 Terminal connection torque	螺丝 M4 根据相应的应用手册进行安装 Screw M4 - Mounting according to valid application note 螺丝 M8 根据相应的应用手册进行安装 Screw M8 - Mounting according to valid application note	M	1,8 8,0	-	2,1 10 Nm
重量 Weight		G		800	g

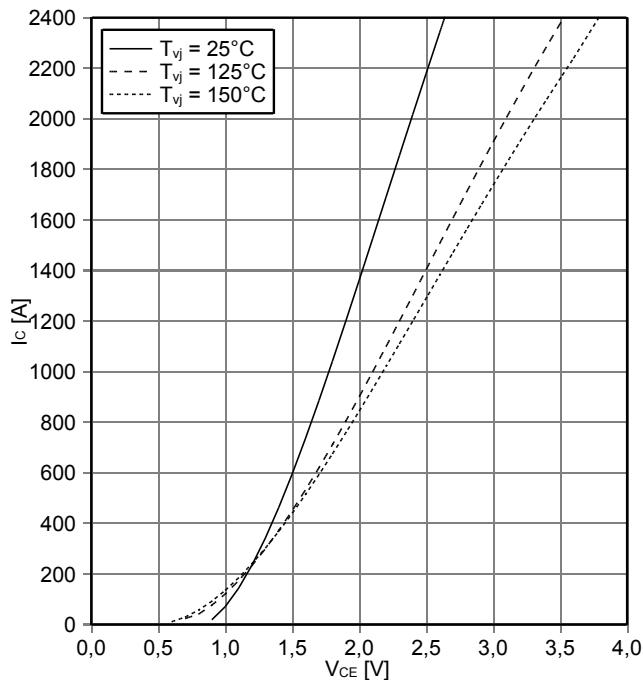
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初步数据
Preliminary Data

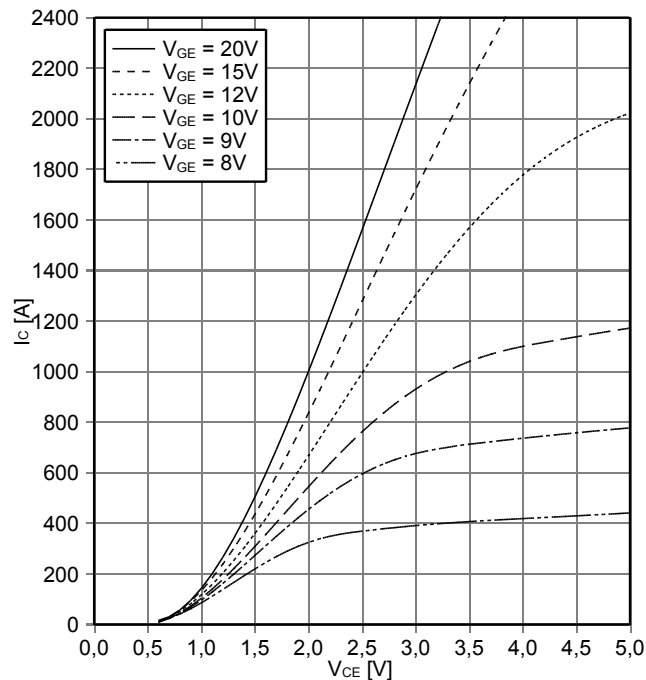
输出特性 IGBT, 制动-斩波器 (典型)
output characteristic IGBT, Brake-Chopper (typical)

$I_C = f(V_{CE})$
 $V_{GE} = 15\text{ V}$



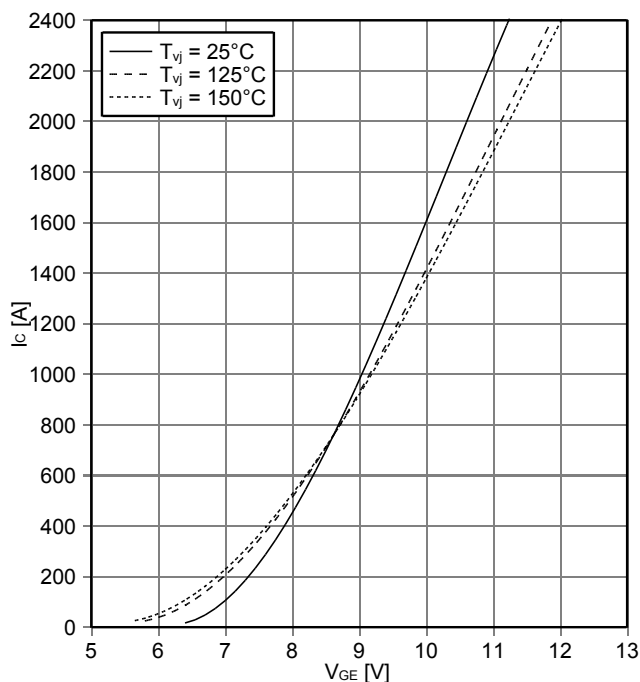
输出特性 IGBT, 制动-斩波器 (典型)
output characteristic IGBT, Brake-Chopper (typical)

$I_C = f(V_{CE})$
 $T_{vj} = 150^\circ\text{C}$



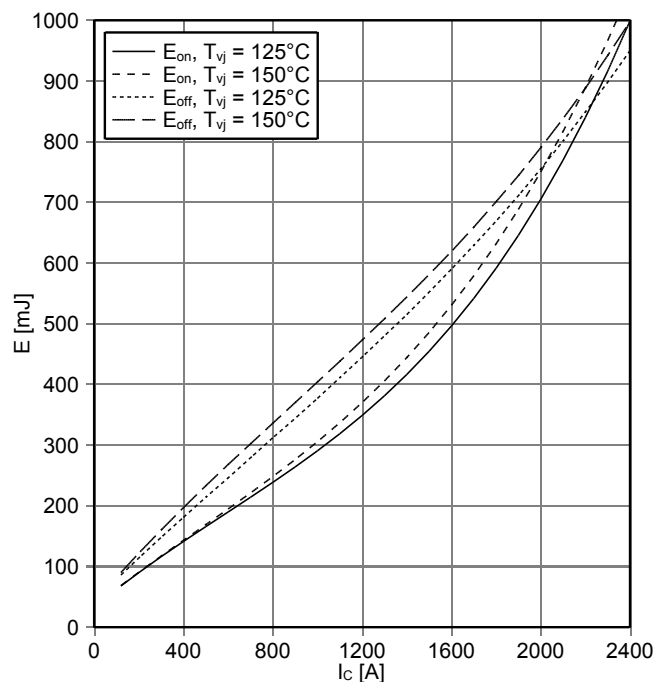
传输特性 IGBT, 制动-斩波器 (典型)
transfer characteristic IGBT, Brake-Chopper (typical)

$I_C = f(V_{GE})$
 $V_{CE} = 20\text{ V}$



开关损耗 IGBT, 制动-斩波器 (典型)
switching losses IGBT, Brake-Chopper (typical)

$E_{on} = f(I_C)$, $E_{off} = f(I_C)$
 $V_{GE} = \pm 15\text{ V}$, $R_{Gon} = 0.22\ \Omega$, $R_{Goff} = 0.9\ \Omega$, $V_{CE} = 900\text{ V}$



prepared by: WB
approved by: PL

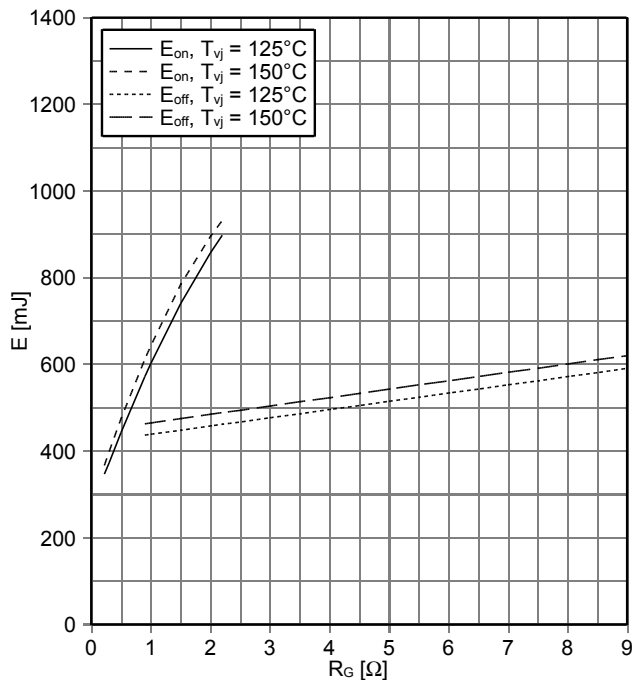
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初步数据
Preliminary Data

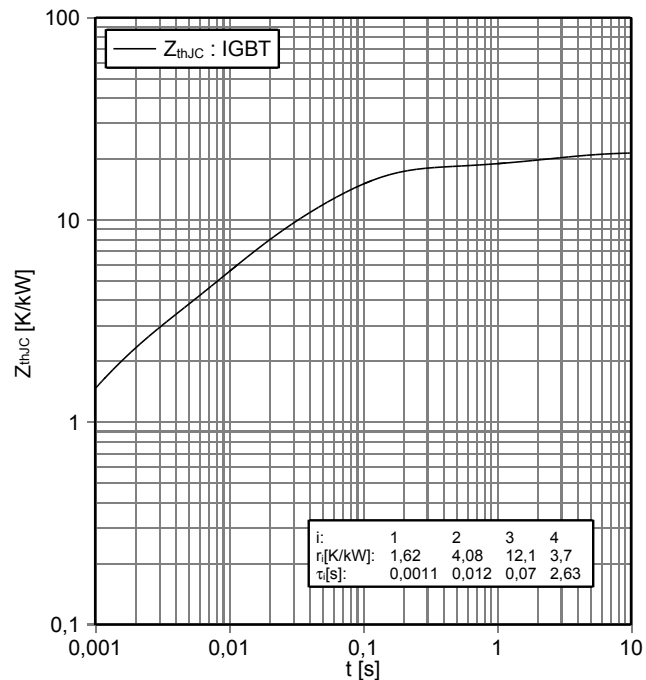
开关损耗 IGBT, 制动-斩波器 (典型)
switching losses IGBT, Brake-Chopper (typical)

$E_{on} = f(R_G), E_{off} = f(R_G)$
 $V_{GE} = \pm 15\text{ V}, I_C = 1200\text{ A}, V_{CE} = 900\text{ V}$



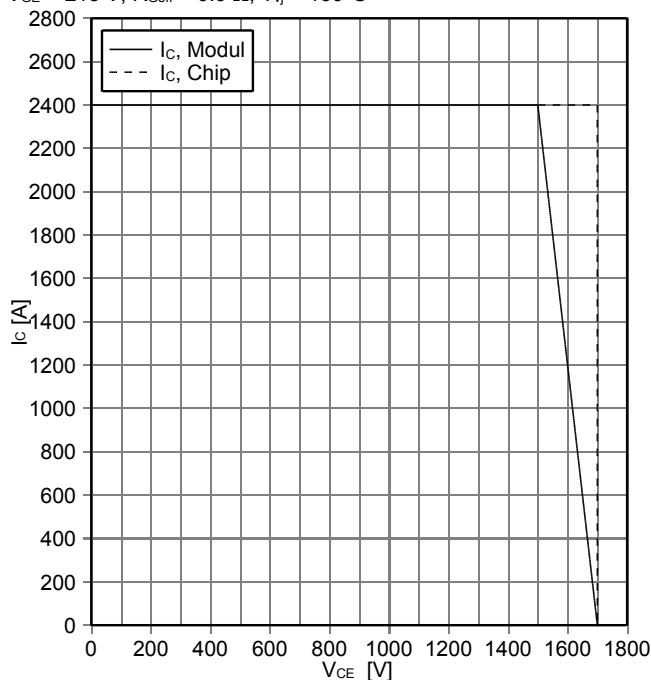
瞬态热阻抗 IGBT, 制动-斩波器
transient thermal impedance IGBT, Brake-Chopper

$Z_{thJC} = f(t)$



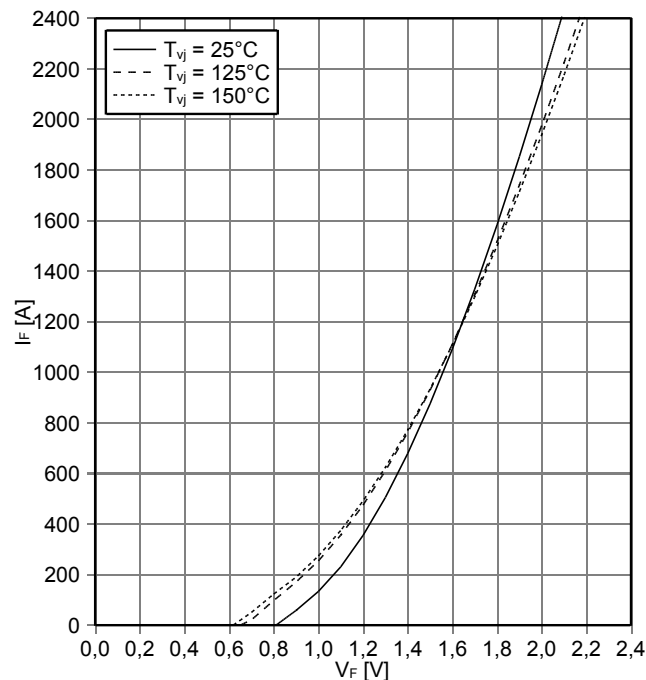
反偏安全工作区 IGBT, 制动-斩波器 (RBSOA)
reverse bias safe operating area IGBT, Brake-Chopper (RBSOA)

$I_C = f(V_{CE})$
 $V_{GE} = \pm 15\text{ V}, R_{Goff} = 0.9\ \Omega, T_{vj} = 150^\circ\text{C}$



正向偏压特性 二极管, 制动-斩波器 (典型)
forward characteristic of Diode, Brake-Chopper (typical)

$I_F = f(V_F)$

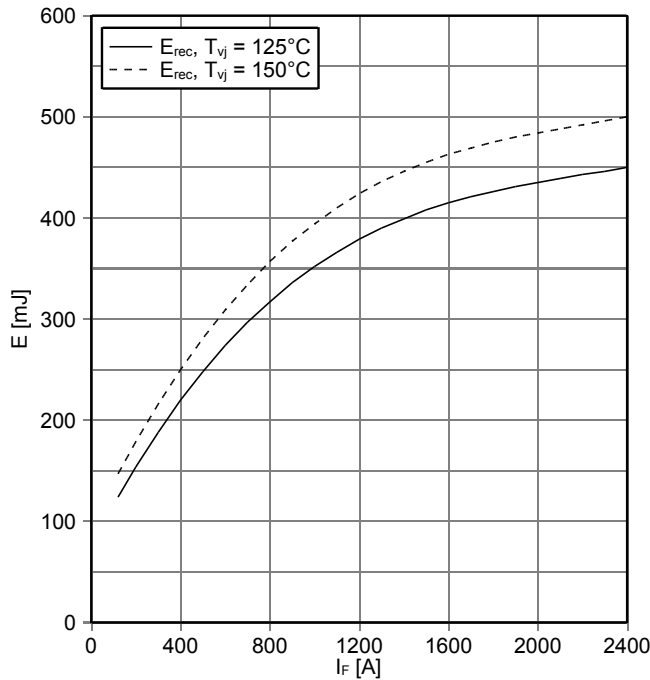


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初步数据
Preliminary Data

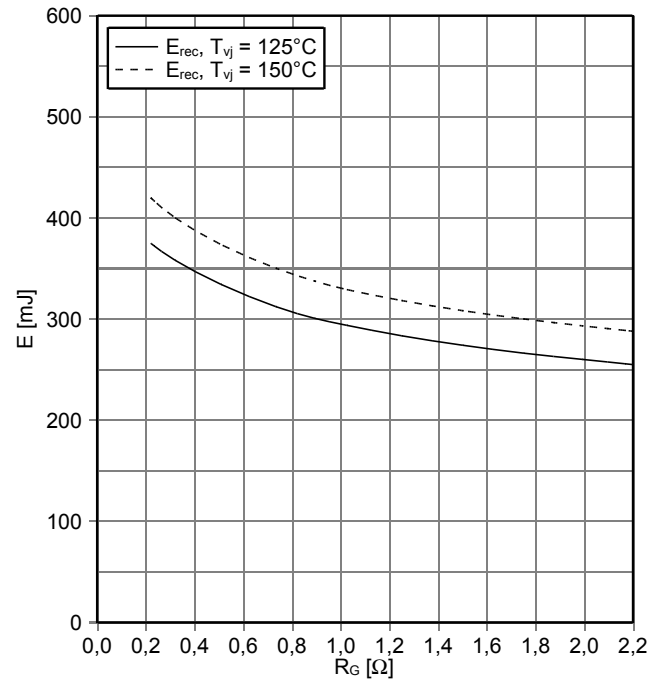
开关损耗 二极管, 制动-斩波器 (典型)
switching losses Diode, Brake-Chopper (typical)

$E_{rec} = f(I_F)$
 $R_{Gon} = 0.22 \Omega, V_{CE} = 900 V$



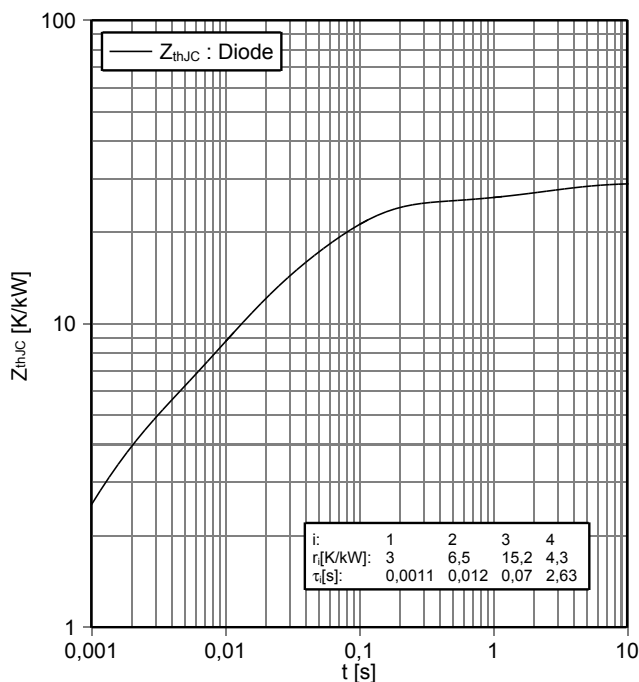
开关损耗 二极管, 制动-斩波器 (典型)
switching losses Diode, Brake-Chopper (typical)

$E_{rec} = f(R_G)$
 $I_F = 1200 A, V_{CE} = 900 V$



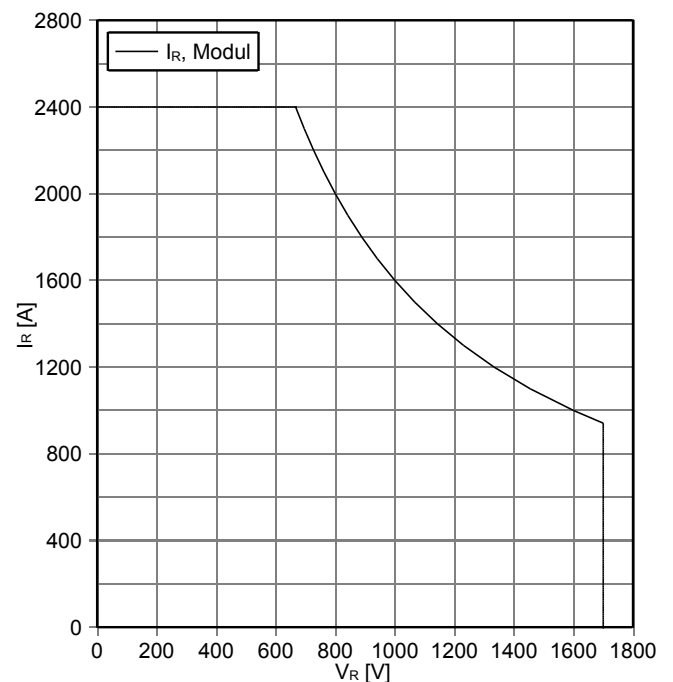
瞬态热阻抗 二极管, 制动-斩波器
transient thermal impedance Diode, Brake-Chopper

$Z_{thJC} = f(t)$



安全工作区 二极管, 制动-斩波器 (SOA)
safe operation area Diode, Brake-Chopper (SOA)

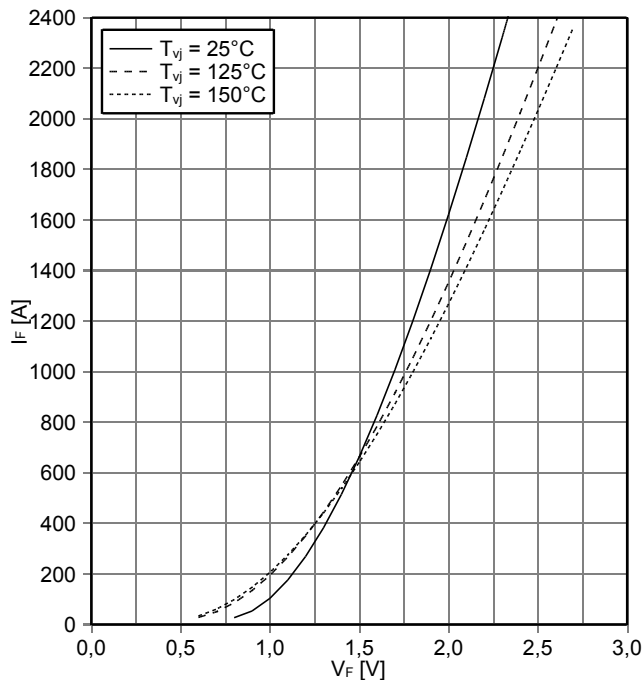
$I_R = f(V_R)$
 $T_{vj} = 150^\circ C$



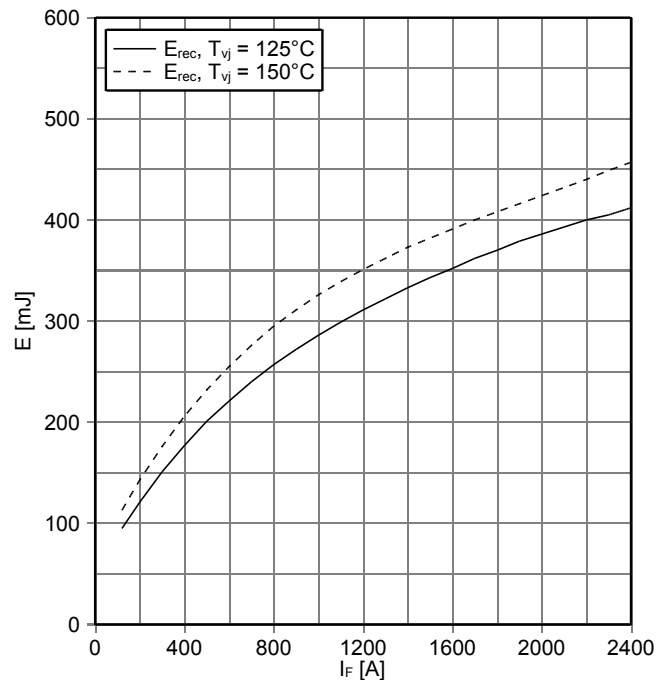


初步数据
Preliminary Data

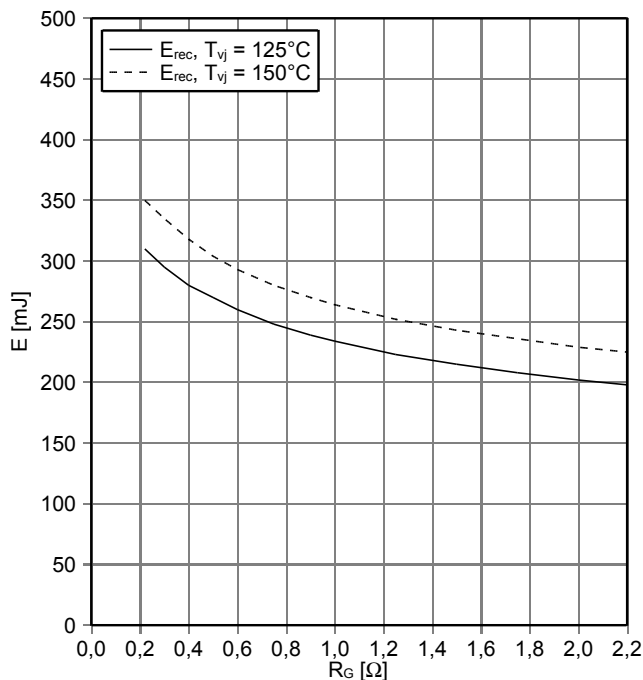
正向偏压特性 反向二极管 (典型)
forward characteristic of Diode, Reverse (typical)
 $I_F = f(V_F)$



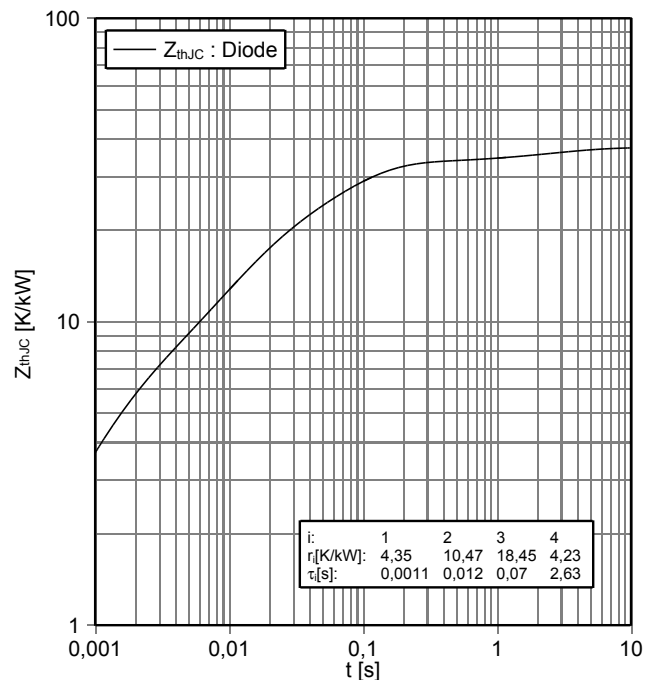
开关损耗 反向二极管 (典型)
switching losses Diode, Reverse (typical)
 $E_{rec} = f(I_F)$
 $R_{Gon} = 0.22 \Omega, V_{CE} = 900 V$



开关损耗 反向二极管 (典型)
switching losses Diode, Reverse (typical)
 $E_{rec} = f(R_G)$
 $I_F = 1200 A, V_{CE} = 900 V$



瞬态热阻抗 反向二极管
transient thermal impedance Diode, Reverse
 $Z_{thJC} = f(t)$

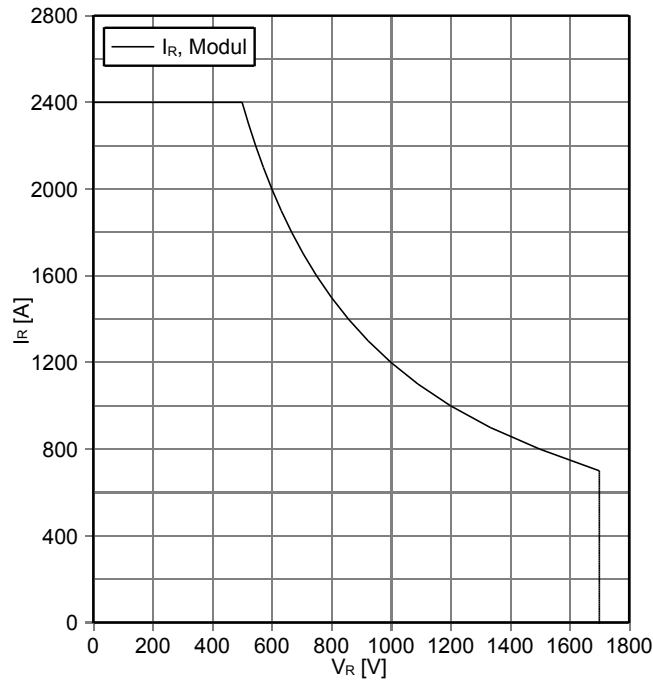


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Preliminary Data

安全工作区 反向二极管 (SOA)
safe operation area Diode, Reverse (SOA)

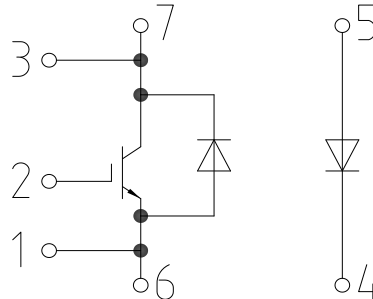
$I_R = f(V_R)$
 $T_{vj} = 150^\circ\text{C}$



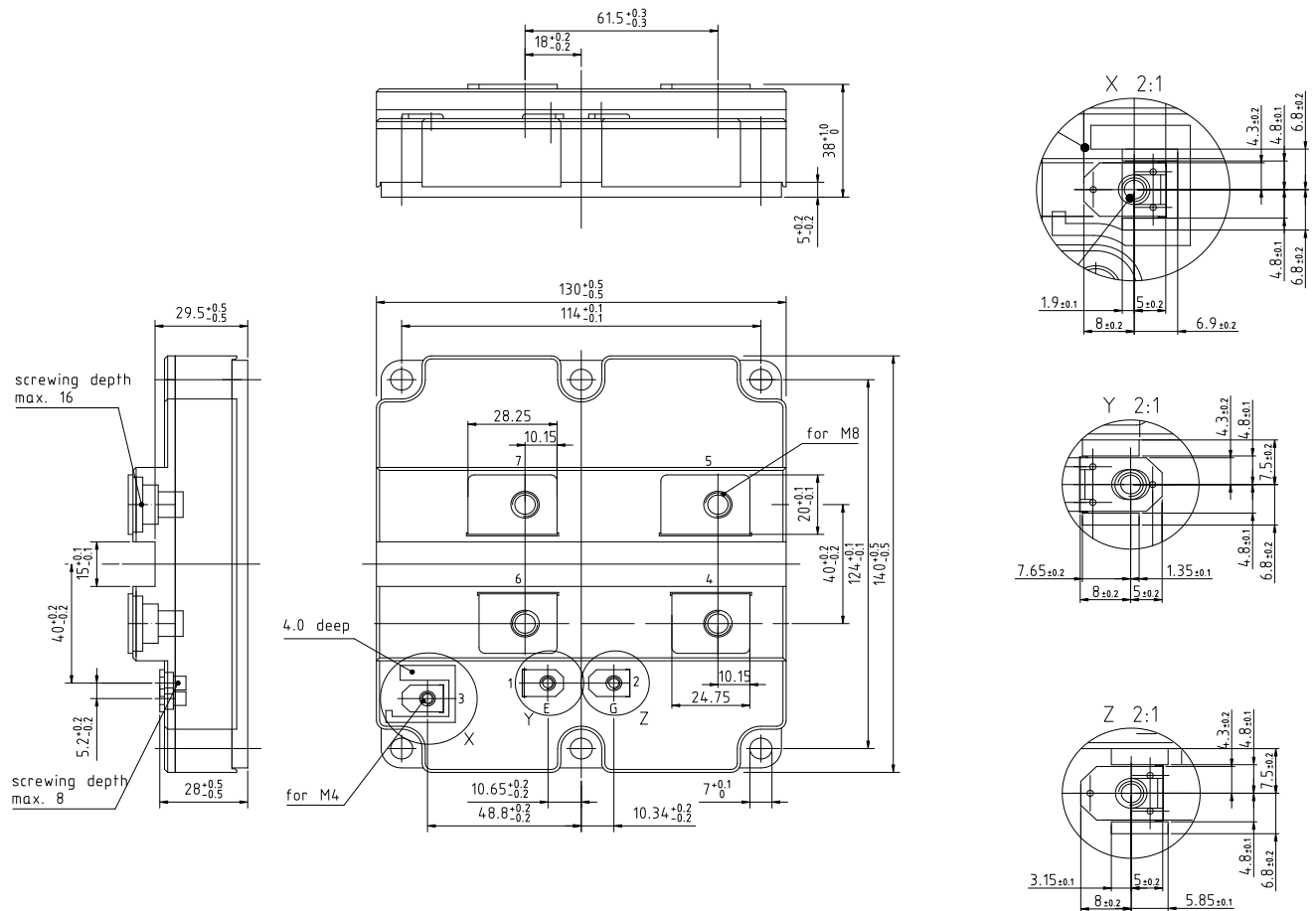
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接线图 / circuit_diagram_headline



封装尺寸 / package outlines



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使用条件和条款

使用条件和条款

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-得到质量协议的结论

-建立联合的测试和出厂产品检查，我们可以根据测试的实际情况供货

如果有必要，请根据实际需要将类似的说明给你的客户

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- the conclusion of Quality Agreements;

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